



TET ESTEL AS
ESTONIA

**October
2015**

**Series
D333-500**

**Rectifier Press-Pack
Diode
Type D333-500**

Designed for rectifiers and industrial applications

Maximum mean forward current	I _{FAV} 500 A					
Maximum repetitive peak reverse voltage	U _{RRM} 2200 ÷ 3200 V					
Reverse recovery time	trr (typ) 30 µs					
U _{RRM} , V	2200	2400	2600	2800	3000	3200
Voltage code	22	24	26	28	30	32
Tvj, °C	- 60 ÷ 150					

MAXIMUM ALLOWABLE RATINGS							
Symbols and parameters			Units	D333-500	Conditions		
I _{FAV}	Mean forward current		A	500 1160	Tc=122 °C, Tc=55 °C, 180° half-sine wave, 50 Hz		
I _{FRMS}	RMS forward current		A	785	Tc=122 °C		
I _{FSM}	Surge forward current		kA	11 12	Tvj=150°C Tvj=25°C	tp=10 ms UR=0	
I ² t	Limiting load integral		kA ² s	605 720	Tvj=150°C Tvj=25°C		
U _{RRM}	Repetitive peak reverse voltage		V	2200÷3200	Tj min≤Tvj≤Tjm 180° half-sine wave, 50 Hz		
U _{RSR}	Non-repetitive peak reverse voltage		V	2300÷3300	Tj min≤Tvj≤Tjm 180° half-sine wave tp=10 ms, Single pulse		
T _{stg}	Storage temperature		°C	-60÷80			
Tvj	Junction temperature		°C	-60÷150			

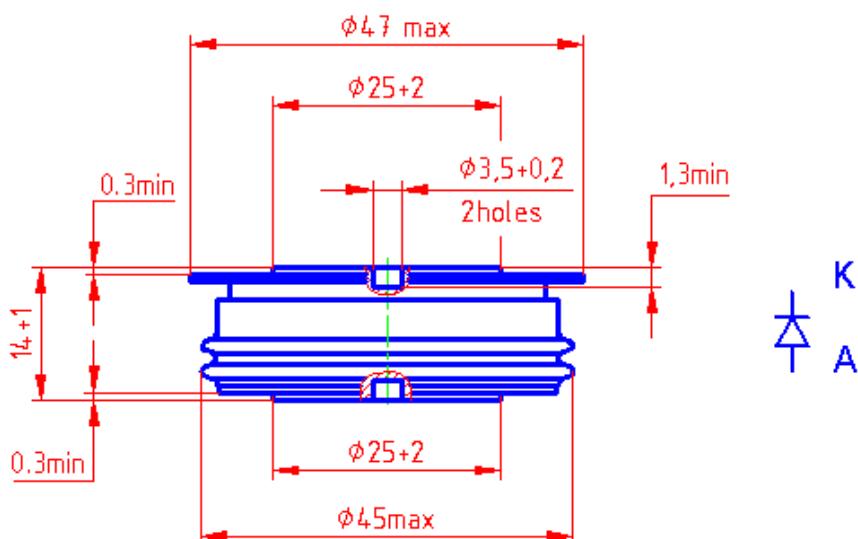
CHARACTERISTICS

U _{FM}	Peak forward voltage	V	1,6	Tvj=25°C, I _{TM} =3,14 I _{FAV}
U _{F(TO)}	Threshold voltage	V	0,9	Tvj=150°C 1,57 I _{FAV} < I _T <4,71 I _{FAV}
R _T	Forward slope resistance	mΩ	0,4	
I _{RRM}	Repetitive peak reverse current	mA	50	Tvj=150°C, UR= U _{RRM}

CHARACTERISTICS				
Symbols and parameters		Units	D333-500	Conditions
Qrr	Recovered charge (typ)	µC	1600	Tvj=150°C If=500 A diR/dt =10 A/µs UR=100V
trr	Reverse recovery time (typ)	µs	30	
Irrm	Peak reverse recovery current (typ)	A	105	
Rthjc	Thermal resistance junction to case	°C/W	0,04	

ORDERING					
	D	333	500	30	
	1	2	3	4	

1. Diode
2. Design version
3. Mean forward current, A
4. Voltage code (30=3000 V)



Mounting force : 8 ÷ 12 kN
Weight : 120 grams